

# **BUK9M35-80E**

## N-channel 80 V, 35 m $\Omega$ logic level MOSFET in LFPAK33 19 September 2016

**Product data sheet** 

#### 1. **General description**

Logic level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

#### 2. **Features and benefits**

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V<sub>GS(th)</sub> rating of greater than 0.5 V at 175 °C

#### **Applications** 3.

- 12 V, 24 V and 48 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

#### Quick reference data

Table 1. Quick reference data

| Symbol                  | Parameter                        | Conditions   |  | Min | Тур | Max | Unit |
|-------------------------|----------------------------------|--|--|-----|-----|-----|------|
| $V_{DS}$                | drain-source voltage             | 25 °C ≤ T <sub>j</sub> ≤ 175 °C  |  | -   | -   | 80  | V    |
| I <sub>D</sub>          | drain current                    | V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>  |  | -   | -   | 26  | Α    |
| P <sub>tot</sub>        | total power dissipation          | T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>   |  | -   | -   | 62  | W    |
| Static chara            | acteristics                      |  |  |     |     |     |      |
| R <sub>DSon</sub>       | drain-source on-state resistance | $V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$  |  | -   | 28  | 35  | mΩ   |
| Dynamic characteristics |                                  |  |  |     |     |     |      |
| $Q_{GD}$                | gate-drain charge                | $I_D = 10 \text{ A}; V_{DS} = 64 \text{ V}; V_{GS} = 5 \text{ V};$<br>$T_j = 25 \text{ °C}; \frac{\text{Fig. } 13}{\text{Fig. } 14}$ |  | -   | 4.9 | -   | nC   |



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# 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--------------------|----------------|
| 1   | S      | Source                            |                    | D              |
| 2   | S      | Source                            |                    |                |
| 3   | S      | Source                            |                    | G T T          |
| 4   | G      | Gate                              |                    | mbb076 S       |
| mb  | D      | Mounting base; connected to drain | LFPAK33 (SOT1210)  |                |

# 6. Ordering information

Table 3. Ordering information

| •           |         |   |         |  |  |  |
|-------------|---------|---|---------|--|--|--|
| Type number | Package |   |         |  |  |  |
|             | Name    | Description   | Version |  |  |  |
| BUK9M35-80E | LFPAK33 | Plastic single ended surface mounted package (LFPAK33); 8 leads | SOT1210 |  |  |  |

# 7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BUK9M35-80E | 93580E       |

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter               | Conditions   |        | Min | Max | Unit |
|------------------|-------------------------|--|--------|-----|-----|------|
| V <sub>DS</sub>  | drain-source voltage    | 25 °C ≤ T <sub>j</sub> ≤ 175 °C                                |        | -   | 80  | V    |
| $V_{DGR}$        | drain-gate voltage      | $R_{GS}$ = 20 k $\Omega$                                       |        | -   | 80  | V    |
| $V_{GS}$         | gate-source voltage     | DC; T <sub>j</sub> ≤ 175 °C                                    |        | -10 | 10  | V    |
|                  |                         | Pulsed; T <sub>j</sub> ≤ 175 °C                                | [1][2] | -15 | 15  | V    |
| P <sub>tot</sub> | total power dissipation | T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>                         |        | -   | 62  | W    |
| I <sub>D</sub>   | drain current           | V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>  |        | -   | 26  | Α    |
|                  |                         | V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u> |        | -   | 19  | Α    |
| I <sub>DM</sub>  | peak drain current      | pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; Fig. 3 |        | -   | 106 | Α    |

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| Symbol               | Parameter                                    | Conditions  |        | Min | Max  | Unit |
|----------------------|--|---|--------|-----|------|------|
| T <sub>stg</sub>     | storage temperature                          |   |        | -55 | 175  | °C   |
| Tj                   | junction temperature                         |   |        | -55 | 175  | °C   |
| Source-dra           | in diode                                     |   |        |     |      |      |
| I <sub>S</sub>       | source current                               | T <sub>mb</sub> = 25 °C   |        | -   | 26   | Α    |
| I <sub>SM</sub>      | peak source current                          | pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$  |        | -   | 106  | Α    |
| Avalanche            | ruggedness                                   |   |        |     |      |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | $I_D$ = 26 A; $V_{sup} \le$ 80 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4 | [3][4] | -   | 32.3 | mJ   |

- [1] Accumulated pulse duration up to 50 hours delivers zero defect ppm.
- [2] Significantly longer life times are achieved by lowering T<sub>i</sub> and or V<sub>GS</sub>
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [4] Refer to application note AN10273 for further information.

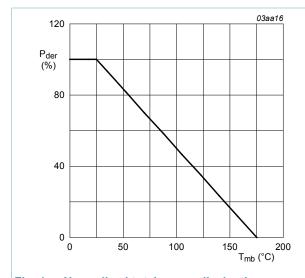


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

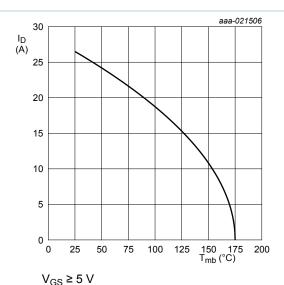
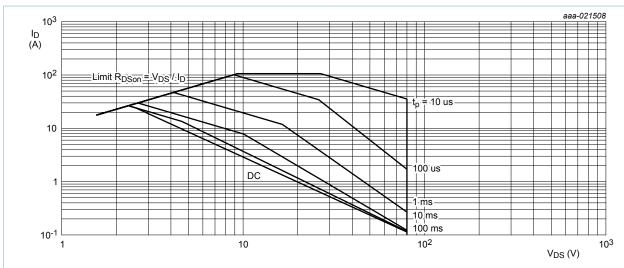


Fig. 2. Continuous drain current as a function of mounting base temperature

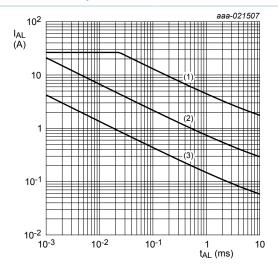
$$I_D = 26A \times \sqrt{\frac{175^{\circ}C - T_{mb}}{150^{\circ}C}}$$
 for  $T_{mb} \ge 25^{\circ}C$ 

#### N-channel 80 V, 35 mΩ logic level MOSFET in LFPAK33



 $T_{mb}$  = 25 °C;  $I_{DM}$  is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1)  $T_{j \text{ (init)}}$  = 25 °C; (2)  $T_{j \text{ (init)}}$  = 150 °C; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

### 9. Thermal characteristics

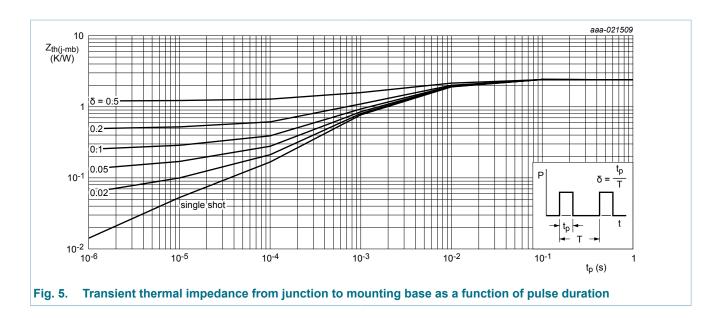
Table 6. Thermal characteristics

| Symbol                | Parameter   | Conditions | Min | Тур  | Max  | Unit |
|-----------------------|---|------------|-----|------|------|------|
| R <sub>th(j-mb)</sub> | thermal resistance<br>from junction to<br>mounting base | Fig. 5     | -   | 2.01 | 2.43 | K/W  |

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### 10. Characteristics

Table 7. Characteristics

| Symbol  | Parameter  | Conditions   | Min | Тур  | Max  | Unit |
|---|--|--|-----|------|------|------|
| Static chara  | acteristics  |  |     |      |      |      |
| V <sub>(BR)DSS</sub> drain-source breakdown voltage |  | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$   | 80  | -    | -    | V    |
|   | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 ^{\circ}C$ | 72   | -   | -    | V    |      |
| V <sub>GS(th)</sub>                                 | gate-source threshold voltage                        | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C;<br>Fig. 9; Fig. 10                | 1.4 | 1.7  | 2.1  | V    |
|   |  | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C;<br>Fig. 10                       | -   | -    | 2.45 | V    |
|   |  | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C;<br>Fig. 10                       | 0.5 | -    | -    | V    |
| I <sub>DSS</sub>                                    | drain leakage current                                | V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                | -   | 0.01 | 1    | μA   |
|   |  | V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C               | -   | -    | 500  | μA   |
| I <sub>GSS</sub> gate leakage cur                   | gate leakage current                                 | V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                | -   | 2    | 100  | nA   |
|   |  | V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C               | -   | 2    | 100  | nA   |
| R <sub>DSon</sub>                                   | drain-source on-state                                | $V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 11$        | -   | 28   | 35   | mΩ   |
|   | resistance   | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u> | -   | 25   | 31   | mΩ   |
|   |  | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 175 °C; <u>Fig. 12</u> | -   | -    | 88   | mΩ   |
| Dynamic ch  | naracteristics                                       |  | ,   |      |      |      |
| Q <sub>G(tot)</sub>                                 | total gate charge                                    | I <sub>D</sub> = 10 A; V <sub>DS</sub> = 64 V; V <sub>GS</sub> = 5 V;                | -   | 13.5 | -    | nC   |
| Q <sub>GS</sub>                                     | gate-source charge                                   | T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>                              | -   | 3.3  | -    | nC   |
| $Q_{GD}$  | gate-drain charge                                    |  | -   | 4.9  | -    | nC   |

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| Symbol              | Parameter                    | Conditions  |  | Min | Тур  | Max  | Unit |
|---------------------|------------------------------|---|--|-----|------|------|------|
| C <sub>iss</sub>    | input capacitance            | $V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$   |  | -   | 1356 | 1804 | pF   |
| C <sub>oss</sub>    | output capacitance           | T <sub>j</sub> = 25 °C; <u>Fig. 15</u>  |  | -   | 106  | 127  | pF   |
| C <sub>rss</sub>    | reverse transfer capacitance |   |  | -   | 52   | 71   | pF   |
| t <sub>d(on)</sub>  | turn-on delay time           | $V_{DS} = 60 \text{ V}; R_L = 5 \Omega; V_{GS} = 5 \text{ V};$ $R_{G(ext)} = 5 \Omega; T_j = 25 \text{ °C}$ |  | -   | 8.8  | -    | ns   |
| t <sub>r</sub>      | rise time                    |   |  | -   | 14   | -    | ns   |
| t <sub>d(off)</sub> | turn-off delay time          |   |  | -   | 19.5 | -    | ns   |
| t <sub>f</sub>      | fall time                    | 1   |  | -   | 12   | -    | ns   |
| Source-dra          | ain diode                    | 1   |  |     |      |      |      |
| V <sub>SD</sub>     | source-drain voltage         | $I_S = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 16$                                     |  | -   | 0.78 | 1.2  | V    |
| t <sub>rr</sub>     | reverse recovery time        | $I_S = 10 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$                           |  | -   | 21   | -    | ns   |
| Q <sub>r</sub>      | recovered charge             | V <sub>DS</sub> = 25 V; T <sub>j</sub> = 25 °C  |  | -   | 21.6 | -    | nC   |

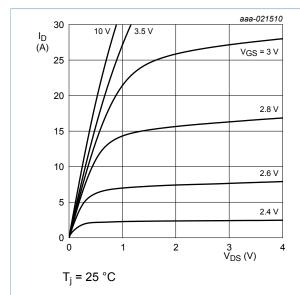


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

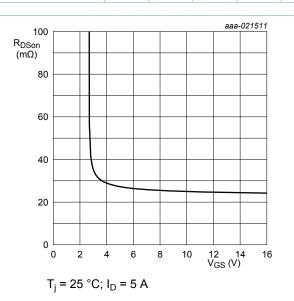


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### N-channel 80 V, 35 m $\Omega$ logic level MOSFET in LFPAK33

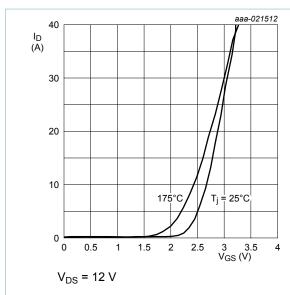


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

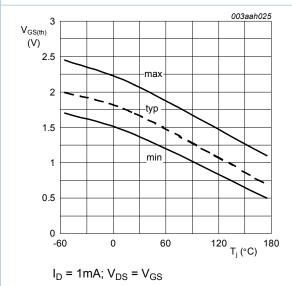


Fig. 10. Gate-source threshold voltage as a function of junction temperature

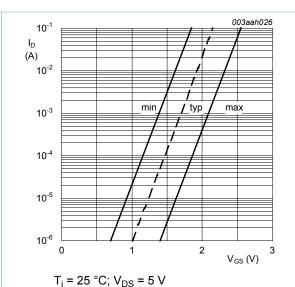


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

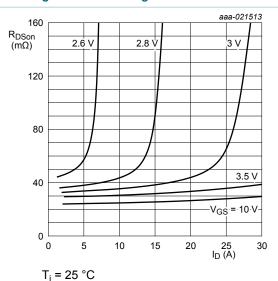


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

#### N-channel 80 V, 35 mΩ logic level MOSFET in LFPAK33

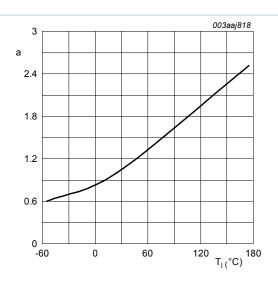


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

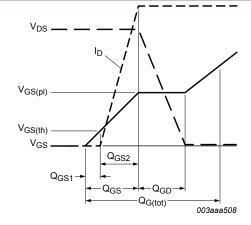
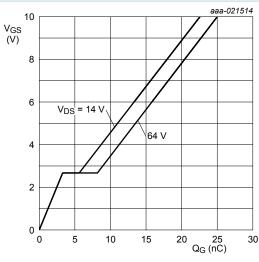
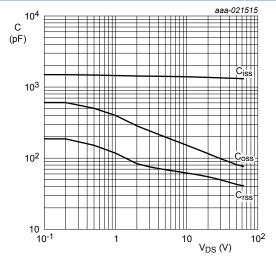


Fig. 14. Gate charge waveform definitions



 $T_i = 25 \,^{\circ}\text{C}; I_D = 10 \,\text{A}$ 

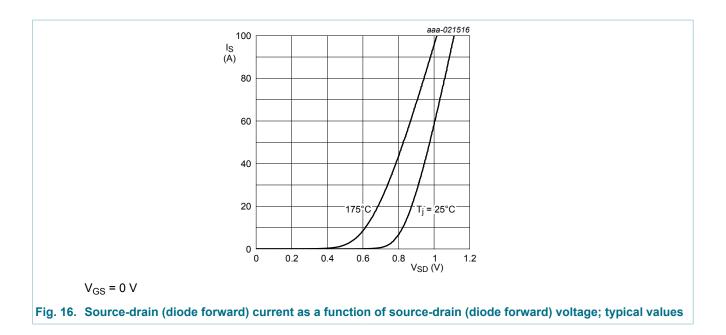
Fig. 13. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0 V$ ; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

#### N-channel 80 V, 35 m $\Omega$ logic level MOSFET in LFPAK33

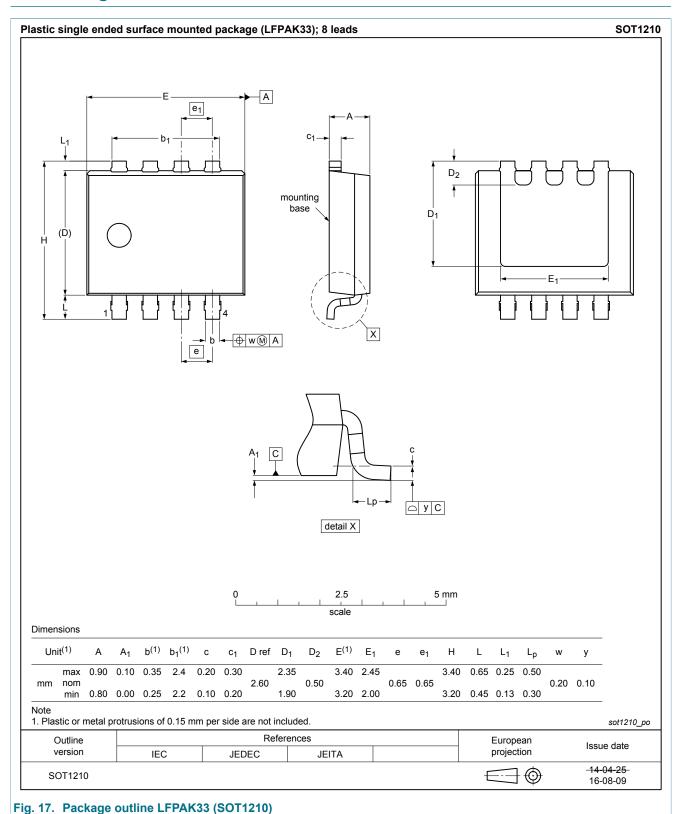


# 11. Application information

For guidance on how to use and understand this datasheet, please refer to application note <a href="Months:AN11158">AN11158</a> "Understanding power MOSFET datasheet parameters".

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## 12. Package outline



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#### N-channel 80 V, 35 mΩ logic level MOSFET in LFPAK33

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|--------------------------------------|--------------------|---|
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| Preliminary<br>[short] data<br>sheet | Qualification      | This document contains data from the preliminary specification.                       |
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### N-channel 80 V, 35 m $\Omega$ logic level MOSFET in LFPAK33

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